

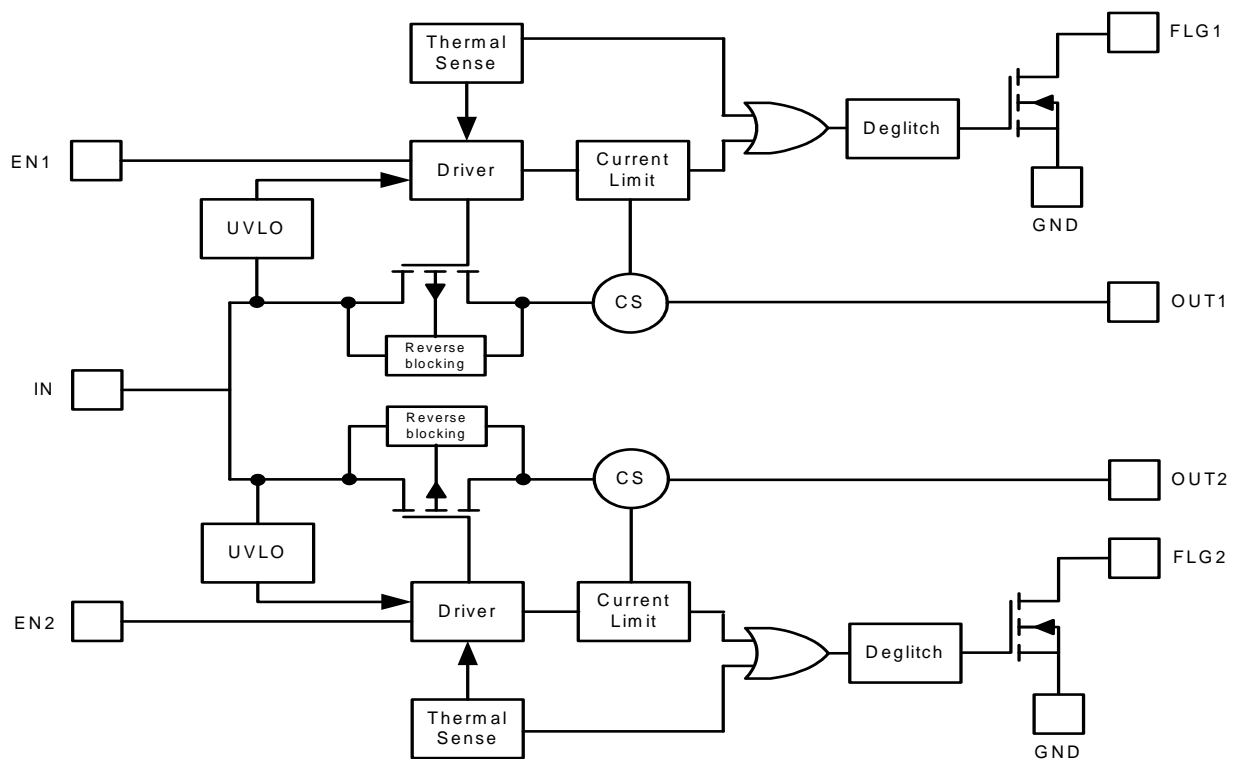
### Available Options

Part Number	Channel	Enable Pin (EN)	Current Limit (typ)	Recommended Maximum Continuous Load Current
AP2186	2	Active Low	2.1A	1.5A
AP2196	2	Active High	2.1A	1.5A

### Pin Descriptions

Pin Name	Pin Number		Function
	SO-8	MSOP-8EP	
EN1	1	1	Switch 1 enable input, active low (AP2186) or active high (AP2196)
FLG1	2	2	Switch 1 over-current and over-temperature fault report, open-drain
FLG2	3	3	Switch 2 over-current and over-temperature fault report, open-drain
EN2	4	4	Switch 2 enable input, active low (AP2186) or active high (AP2196)
OUT2	5	5	Switch 2 voltage output pin
GND	6	6	Ground
IN	7	7	Voltage input pin
OUT1	8	8	Switch 1 voltage output pin
Exposed Pad	—	Exposed Pad	Exposed Pad: It should be connected externally to GND and thermal mass for enhanced thermal impedance. It should not be used as electrical ground conduction path.

### Functional Block Diagram



## Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Symbol	Parameter	Rating	Unit
ESD HBM	Human Body Model ESD Protection	6	kV
ESD MM	Machine Model ESD Protection	300	V
V <sub>IN</sub>	Input Voltage	6.5	V
V <sub>OUT</sub>	Output Voltage	V <sub>IN</sub> +0.3	V
V <sub>EN</sub> , V <sub>FLG</sub>	Enable Voltage	6.5	V
I <sub>LOAD</sub>	Maximum Continuous Load Current	Internal Limited	A
T <sub>J(MAX)</sub>	Maximum Junction Temperature	150	°C
T <sub>ST</sub>	Storage Temperature Range (Note 4)	-65 to +150	°C

Note: 4. UL Recognized Rating from -30°C to +70°C (Diodes qualified T<sub>ST</sub> from -65°C to +150°C)

## Recommended Operating Conditions (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Symbol	Parameter	Min	Max	Units
V <sub>IN</sub>	Input voltage	2.7	5.5	V
I <sub>OUT</sub>	Output Current	0	1.5	A
V <sub>IL</sub>	EN Input Logic Low Voltage	0	0.8	V
V <sub>IH</sub>	EN Input Logic High Voltage	2.0	V <sub>IN</sub>	V
T <sub>A</sub>	Operating Ambient Temperature	-40	+85	°C

# Electrical Characteristics (@T<sub>A</sub> = +25°C, C<sub>IN</sub> = 10μF, V<sub>IN</sub> = +5V, unless otherwise specified.)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V <sub>UVLO</sub>	Input UVLO	R <sub>LOAD</sub> = 1kΩ	1.6	1.9	2.5	V
I <sub>SHDN</sub>	Input Shutdown Current	Disabled, I <sub>OUT</sub> = 0		0.5	1	μA
I <sub>Q</sub>	Input Quiescent Current, Dual	Enabled, I <sub>OUT</sub> = 0		95	140	μA
I <sub>LEAK</sub>	Input Leakage Current	Disabled, OUT grounded			1	μA
I <sub>REV</sub>	Reverse Leakage Current	Disabled, V <sub>IN</sub> = 0V, V <sub>OUT</sub> = 5V, I <sub>REV</sub> at V <sub>IN</sub>		1		μA
R <sub>DS(ON)</sub>	Switch On-Resistance	V <sub>IN</sub> = 5V, I <sub>OUT</sub> = 1.5A, -40°C ≤ T <sub>A</sub> ≤ +85°C		90	135	mΩ
		MSOP-8EP		100	135	mΩ
		SO-8		120	160	mΩ
I <sub>SHORT</sub>	Short-Circuit Current Limit	Enabled into short circuit, C <sub>L</sub> = 68μF		2.1		A
I <sub>LIMIT</sub>	Over-Load Current Limit	V <sub>IN</sub> = 5V, V <sub>OUT</sub> = 4.5V, C <sub>L</sub> = 120μF, -40°C ≤ T <sub>A</sub> ≤ +85°C	1.6	2.1	2.6	A
I <sub>Trig</sub>	Current Limiting Trigger Threshold	V <sub>IN</sub> = V <sub>EN</sub> , Output Current Slew rate (<100A/WS), C <sub>L</sub> = 68μF		2.5		A
T <sub>SHORT</sub>	Short-Circuit Response Time	V <sub>OUT</sub> = 0V to I <sub>OUT</sub> = I <sub>LIMIT</sub> (short applied to output), C <sub>L</sub> = 68μF		20		μs
V <sub>IL</sub>	EN Input Logic Low Voltage	V <sub>IN</sub> = 2.7V to 5.5V			0.8	V
V <sub>IH</sub>	EN Input Logic High Voltage	V <sub>IN</sub> = 2.7V to 5.5V	2			V
I <sub>SINK</sub>	EN Input Leakage	V <sub>EN</sub> = 5V			1	μA
T <sub>D(ON)</sub>	Output Turn-On Delay Time	C <sub>L</sub> = 1μF, R <sub>LOAD</sub> = 10Ω		0.05		ms
T <sub>R</sub>	Output Turn-On Rise Time	C <sub>L</sub> = 1μF, R <sub>LOAD</sub> = 10Ω		0.6	1.5	ms
T <sub>D(OFF)</sub>	Output Turn-Off Delay Time	C <sub>L</sub> = 1μF, R <sub>LOAD</sub> = 10Ω		0.01		ms
T <sub>F</sub>	Output Turn-Off Fall Time	C <sub>L</sub> = 1μF, R <sub>LOAD</sub> = 10Ω		0.05	0.1	ms
R <sub>FLG</sub>	FLG Output FET On-Resistance	I <sub>FLG</sub> = 10mA		20	40	Ω
I <sub>FOH</sub>	Error Flag Off Current	V <sub>FLG</sub> = 5V		0.01	1	μA
T <sub>Blank</sub>	FLG Blanking Time	C <sub>L</sub> = 68μF	4	7	15	ms
T <sub>SHDN</sub>	Thermal Shutdown Threshold	Enabled, R <sub>LOAD</sub> = 1kΩ		140		°C
T <sub>HYS</sub>	Thermal Shutdown Hysteresis			25		°C
θ <sub>JA</sub>	Thermal Resistance Junction-to-Ambient	SO-8 (Note 5)		110		°C/W
		MSOP-8EP (Note 6)		60		°C/W

Notes: 5. Test condition for SO-8: Device mounted on FR-4 2-layer board, 2oz copper, with minimum recommended pad layout.  
6. Test condition for MSOP-8EP: Device mounted on FR-4 2-layer board, 2oz copper, with minimum recommended pad on top layer and 3 vias to bottom layer ground plane.

## Typical Performance Characteristics

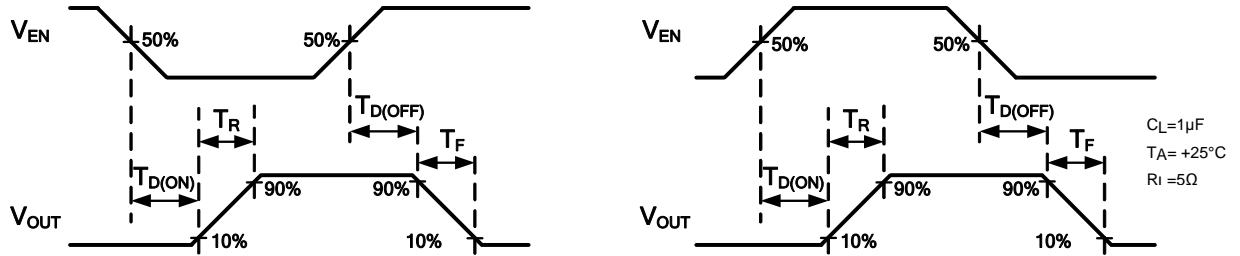
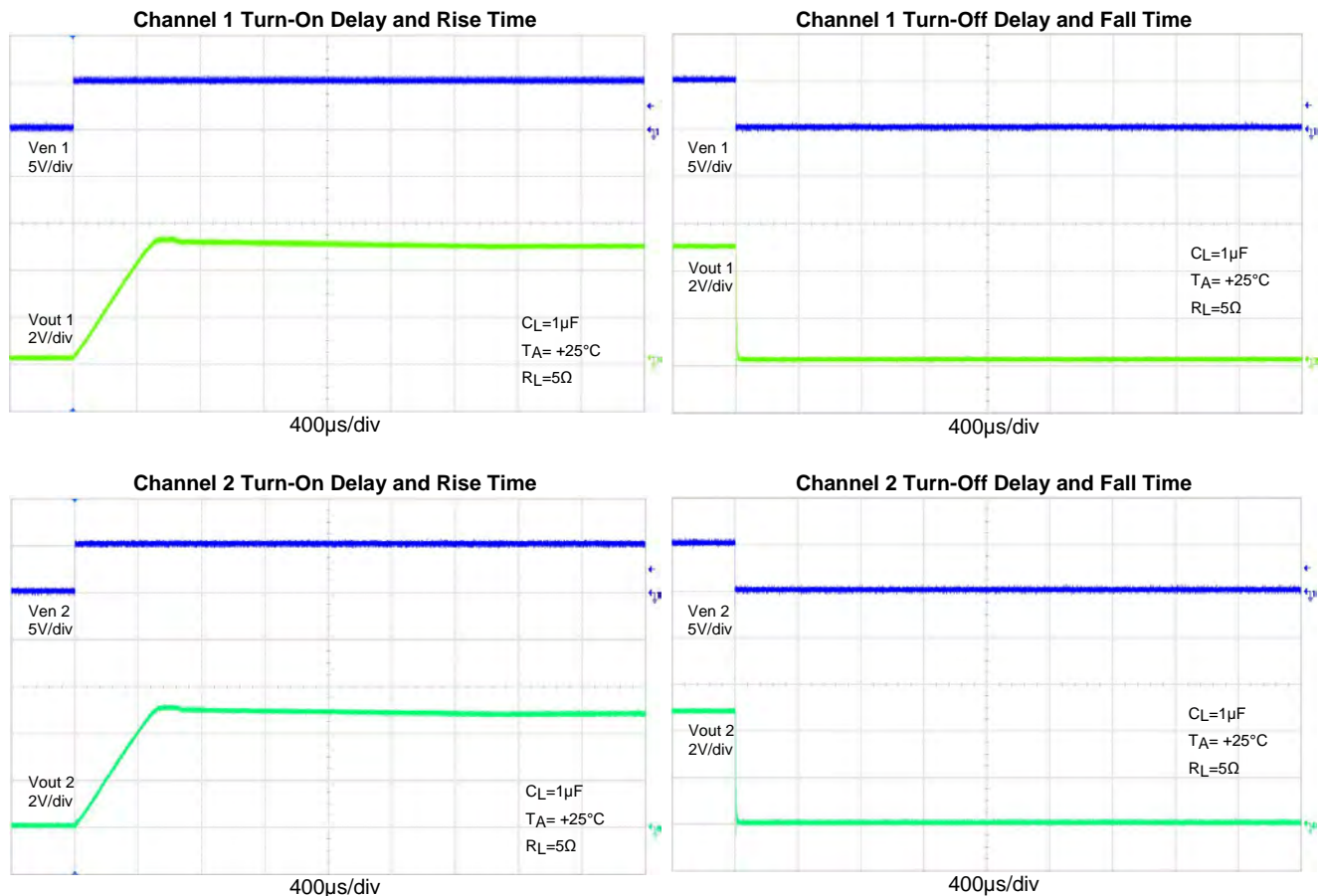


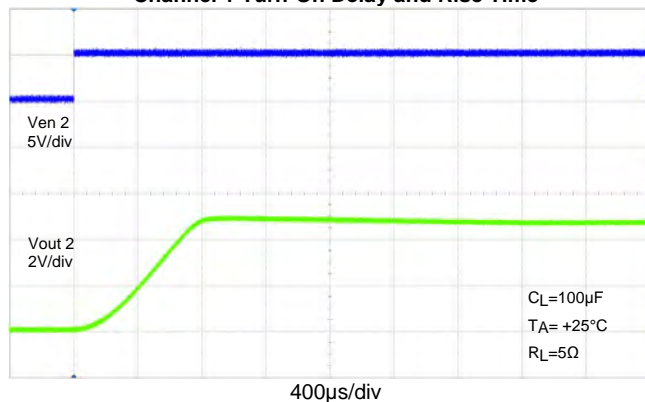
Figure 1 Voltage Waveforms: AP2186 (left), AP2196 (right)

All Enable Plots are for AP2196 Active High

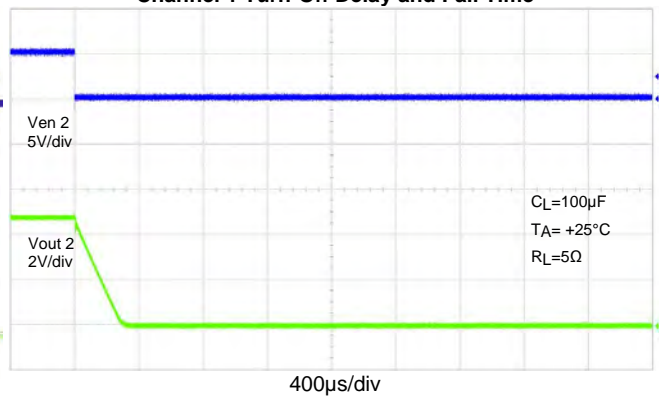


## Typical Performance Characteristics (cont.)

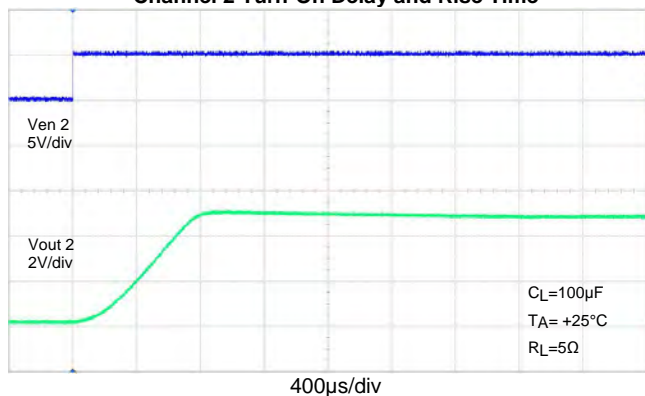
Channel 1 Turn-On Delay and Rise Time



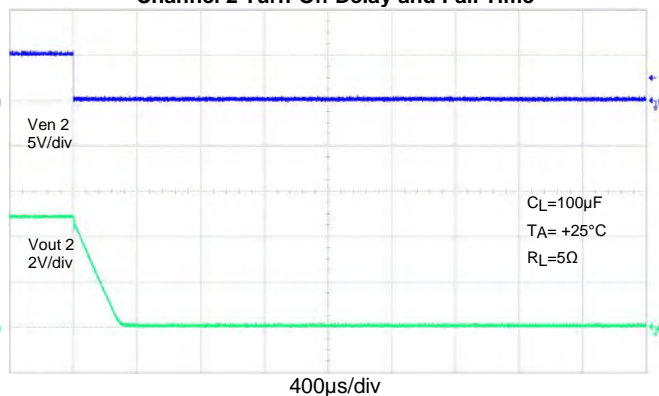
Channel 1 Turn-Off Delay and Fall Time



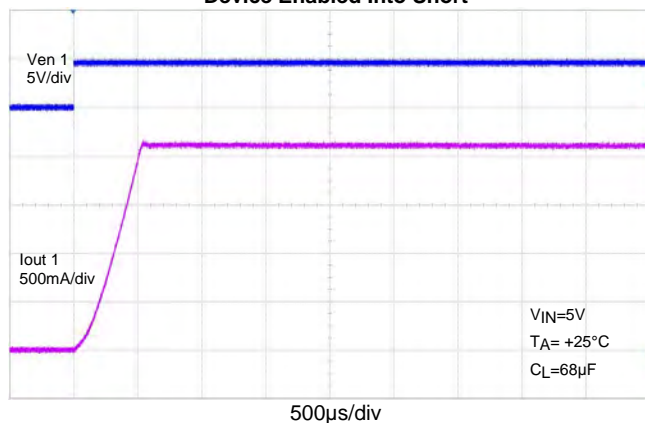
Channel 2 Turn-On Delay and Rise Time



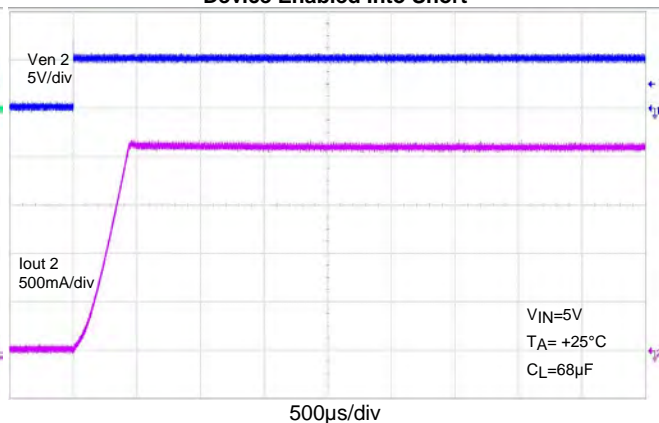
Channel 2 Turn-Off Delay and Fall Time



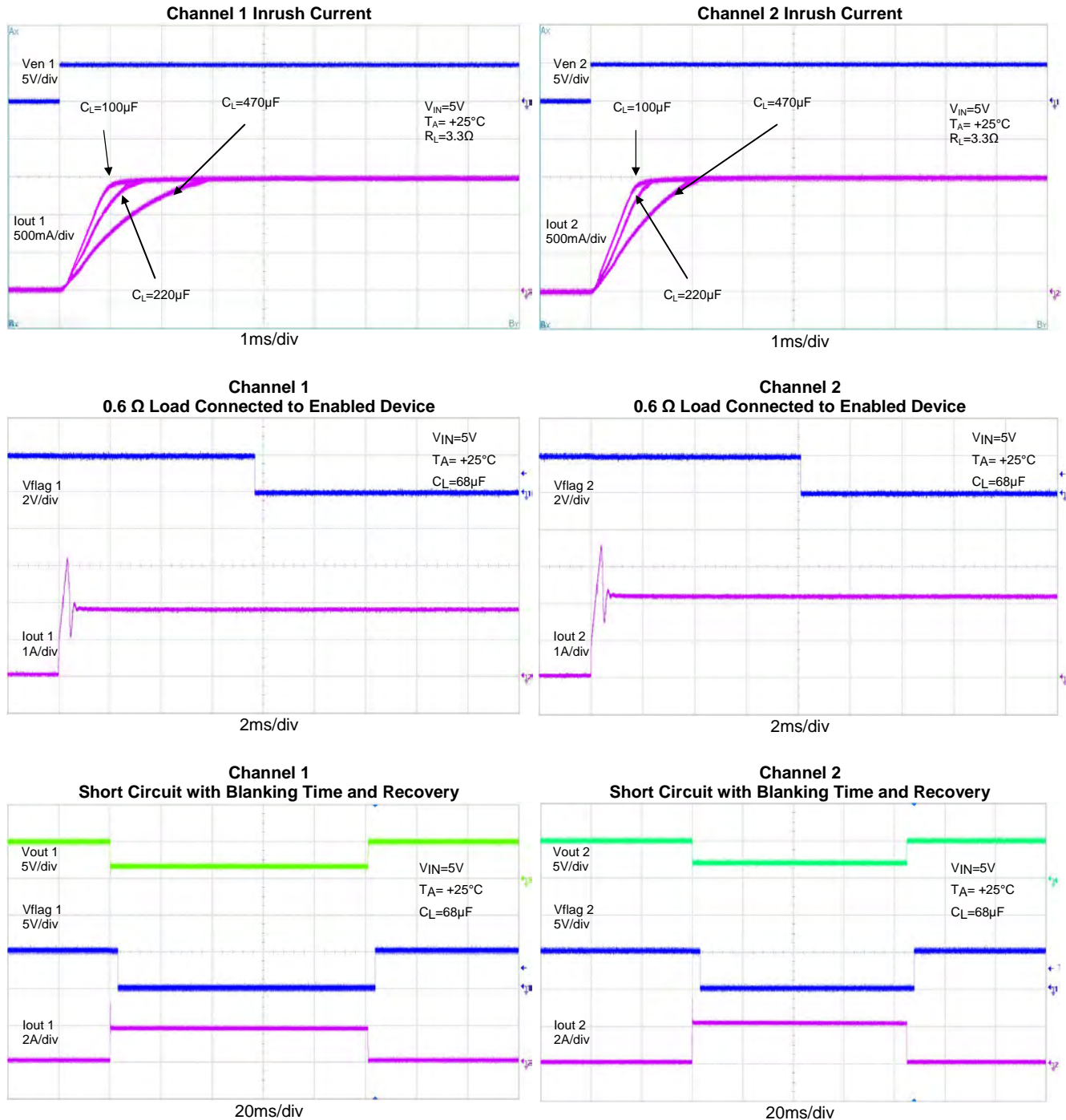
Channel 1 Short Circuit Current,  
Device Enabled Into Short



Channel 2 Short Circuit Current,  
Device Enabled Into Short

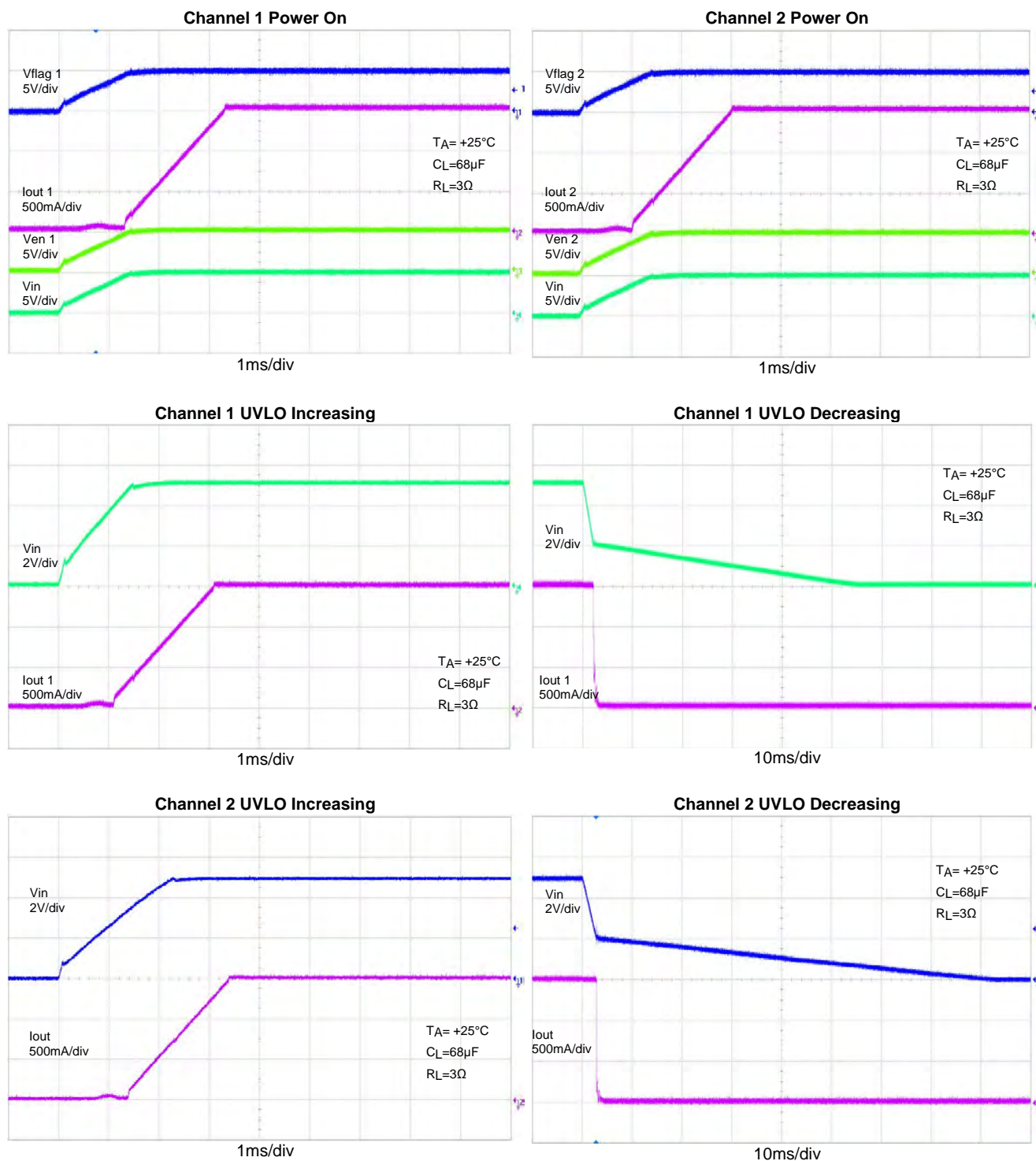


## Typical Performance Characteristics (cont.)



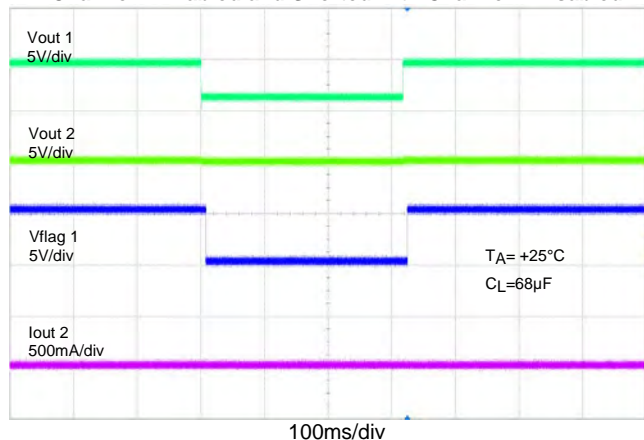


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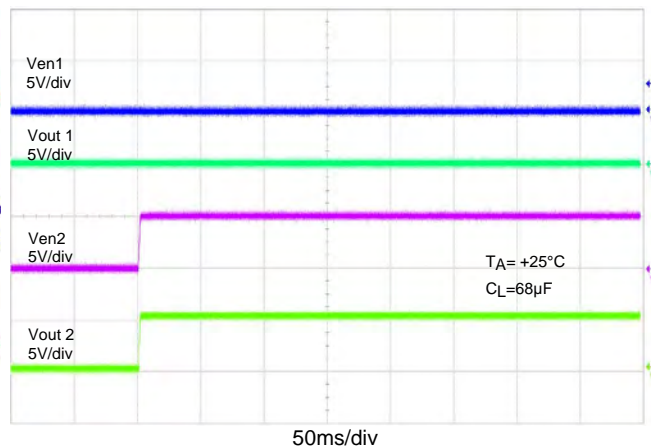


## Typical Performance Characteristics (cont.)

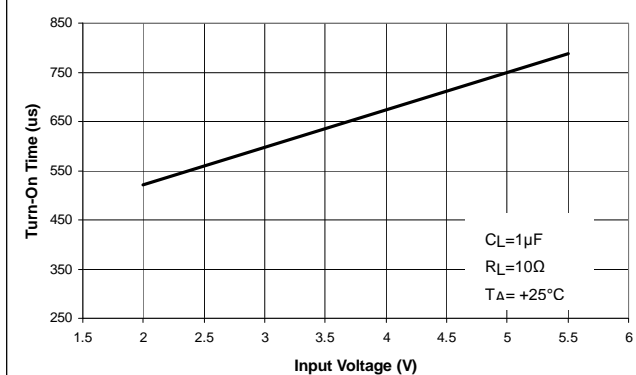
Channel 1 Enabled and Shorted with Channel 2 Disabled



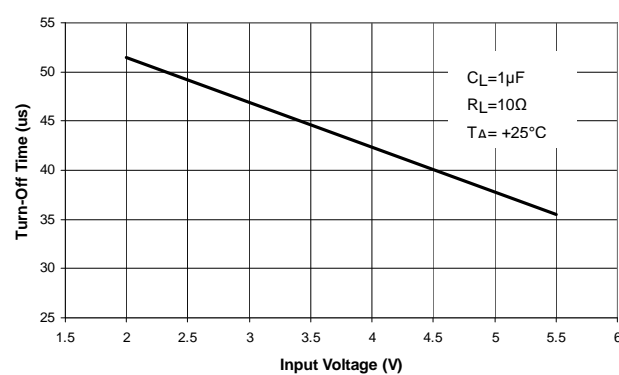
Channel 1 Disabled and Channel 2 Enabled



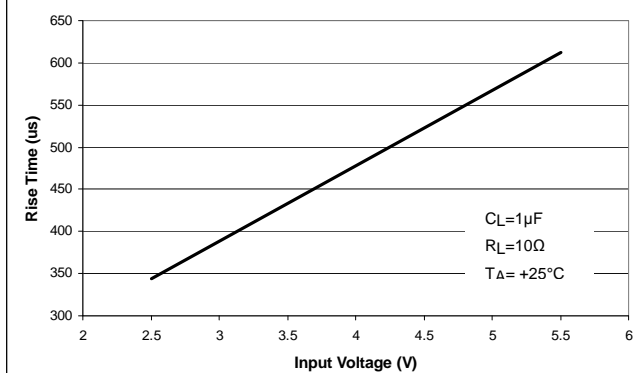
Turn-On Time vs Input Voltage



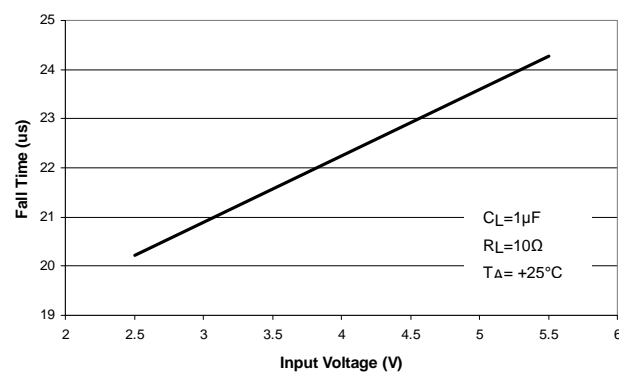
Turn-Off Time vs Input Voltage



Rise Time vs Input Voltage

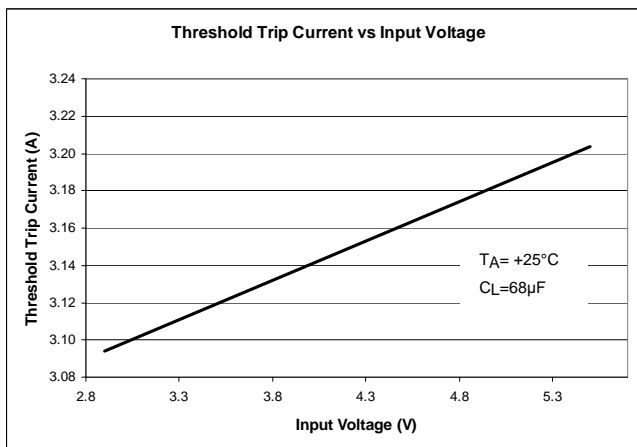
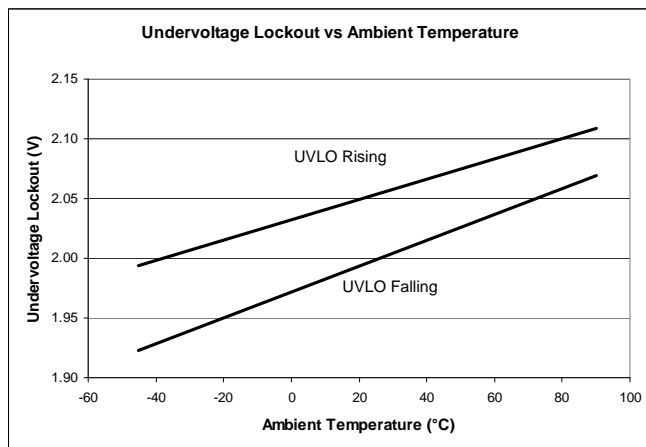
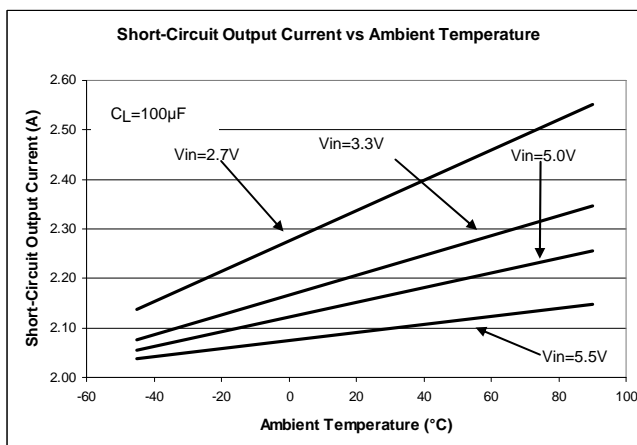
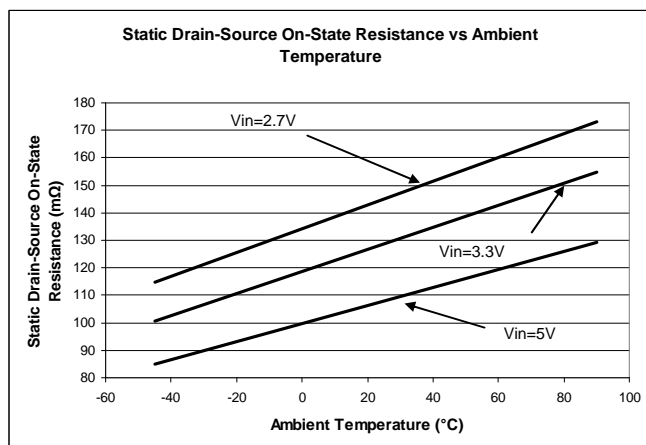
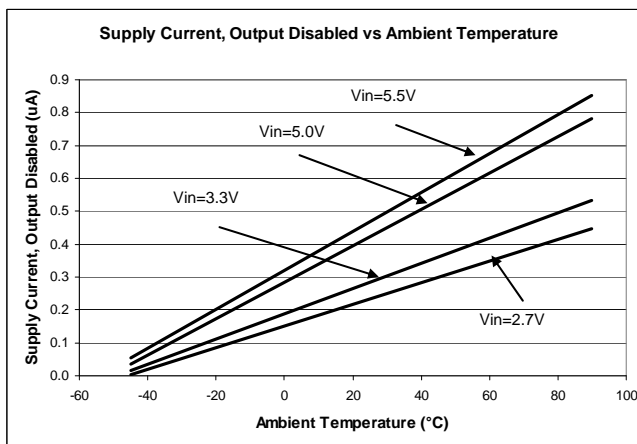
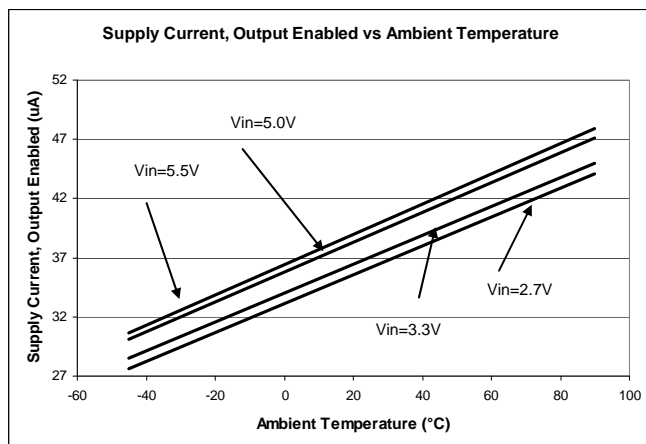


Fall Time vs Input Voltage

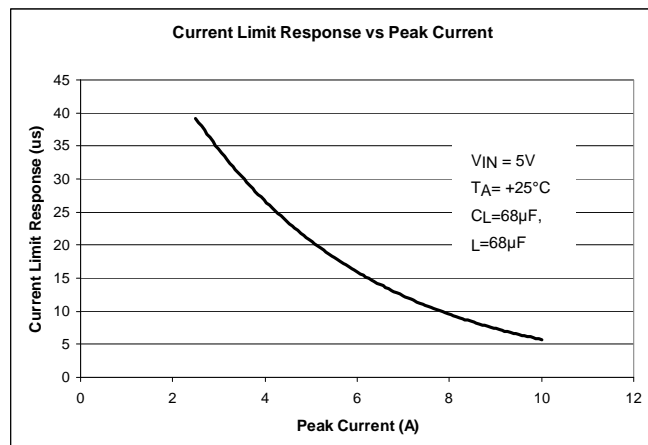




## Typical Performance Characteristics (cont.)



## Typical Performance Characteristics (cont.)



## Application Information

### Power Supply Considerations

A 0.01-μF to 0.1-μF X7R or X5R ceramic bypass capacitor between IN and GND, close to the device, is recommended. Placing a high-value electrolytic capacitor on the input (10-μF minimum) and output pin(s) is recommended when the output load is heavy. This precaution reduces power-supply transients that may cause ringing on the input. Additionally, bypassing the output with a 0.01-μF to 0.1-μF ceramic capacitor improves the immunity of the device to short-circuit transients.

### Over-Current and Short Circuit Protection

An internal sensing FET is employed to check for over-current conditions. Unlike current-sense resistors, sense FETs do not increase the series resistance of the current path. When an overcurrent condition is detected, the device maintains a constant output current and reduces the output voltage accordingly. Complete shutdown occurs only if the fault stays long enough to activate thermal limiting.

Three possible overload conditions can occur. In the first condition, the output has been shorted to GND before the device is enabled or before  $V_{IN}$  has been applied. The AP2186/AP2196 senses the short circuit and immediately clamps output current to a certain safe level namely  $I_{LIMIT}$ .

In the second condition, an output short or an overload occurs while the device is enabled. At the instance the overload occurs, higher current may flow for a very short period of time before the current limit function can react. After the current limit function has tripped (reached the over-current trip threshold), the device switches into current limiting mode and the current is clamped at  $I_{LIMIT}$ .

In the third condition, the load has been gradually increased beyond the recommended operating current. The current is permitted to rise until the current-limit threshold ( $I_{TRIG}$ ) is reached or until the thermal limit of the device is exceeded. The AP2186/AP2196 is capable of delivering current up to the current-limit threshold without damaging the device. Once the threshold has been reached, the device switches into its current limiting mode and is set at  $I_{LIMIT}$ .

Note that when the output has been shorted to GND at extremely low temperature ( $< -30^{\circ}\text{C}$ ), a minimum 120-μF electrolytic capacitor on the output pin is recommended. A correct capacitor type with capacitor voltage rating and temperature characteristics must be properly chosen so that capacitance value does not drop too low at the extremely low temperature operation. A recommended capacitor should have temperature characteristics of less than 10% variation of capacitance change when operated at extremely low temp. Our recommended aluminum electrolytic capacitor type is Panasonic FC series.

### FLG Response

When an over-current or over-temperature shutdown condition is encountered, the FLG open-drain output goes active low after a nominal 7-ms deglitch timeout. The FLG output remains low until both over-current and over-temperature conditions are removed. Connecting a heavy capacitive load to the output of the device can cause a momentary over-current condition, which does not trigger the FLG due to the 7-ms deglitch timeout. The AP2186/AP2196 is designed to eliminate false over-current reporting without the need of external components to remove unwanted pulses.

### Power Dissipation and Junction Temperature

The low on-resistance of the internal MOSFET allows the small surface-mount packages to pass large current. Using the maximum operating ambient temperature ( $T_A$ ) and  $R_{DS(ON)}$ , the power dissipation can be calculated by:

$$P_D = R_{DS(ON)} \times I^2$$

Finally, calculate the junction temperature:

$$T_J = P_D \times R_{\theta JA} + T_A$$

Where:

$T_A$  = Ambient temperature  $^{\circ}\text{C}$

$R_{\theta JA}$  = Thermal resistance

$P_D$  = Total power dissipation

### Thermal Protection

Thermal protection prevents the IC from damage when heavy-overload or short-circuit faults are present for extended periods of time. The AP2186/AP2196 implements a thermal sensing to monitor the operating junction temperature of the power distribution switch. Once the die temperature rises to approximately  $140^{\circ}\text{C}$  due to excessive power dissipation in an over-current or short-circuit condition the internal thermal sense circuitry turns the power switch off, thus preventing the power switch from damage. Hysteresis is built into the thermal sense circuit allowing the device to cool down approximately  $25^{\circ}\text{C}$  before the switch turns back on. The switch continues to cycle in this manner until the load fault or input power is removed. The FLG open-drain output is asserted when an over-temperature shutdown or over-current occurs with 7-ms deglitch.

## Application Information (cont.)

### Under-Voltage Lockout (UVLO)

Under-voltage lockout function (UVLO) keeps the internal power switch from being turned on until the power supply has reached at least 1.9V, even if the switch is enabled. Whenever the input voltage falls below approximately 1.9V, the power switch is quickly turned off. This facilitates the design of hot-insertion systems where it is not possible to turn off the power switch before input power is removed.

### Host/Self-Powered HUBs

Hosts and self-powered hubs (SPH) have a local power supply that powers the embedded functions and the downstream ports (see Figure 2). This power supply must provide from 5.25V to 4.75V to the board side of the downstream connection under both full-load and no-load conditions. Hosts and SPHs are required to have current-limit protection and must report over-current conditions to the USB controller. Typical SPHs are desktop PCs, monitors, printers, and stand-alone hubs.

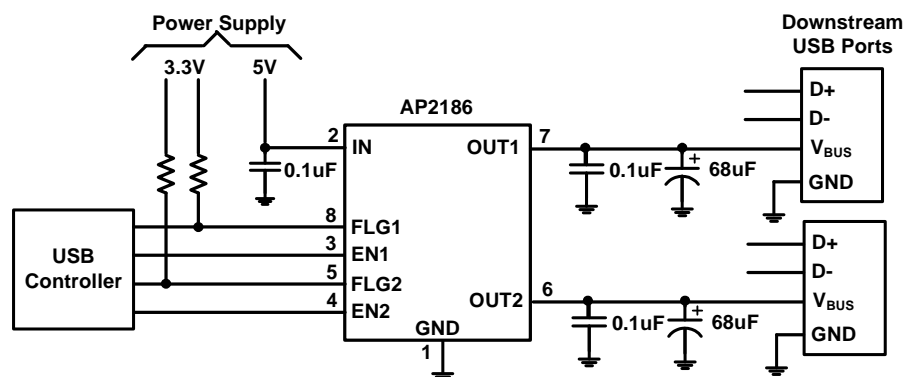


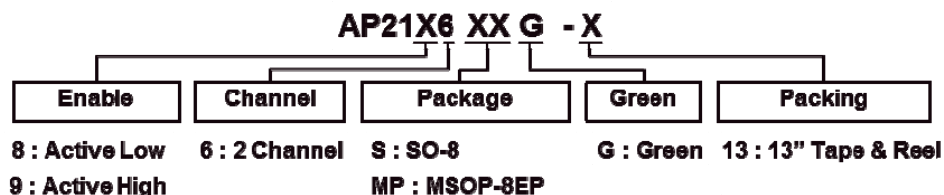
Figure 2 Typical Two-Port USB Host / Self-Powered Hub

### Generic Hot-Plug Applications

In many applications it may be necessary to remove modules or pc boards while the main unit is still operating. These are considered hot-plug applications. Such implementations require the control of current surges seen by the main power supply and the card being inserted. The most effective way to control these surges is to limit and slowly ramp the current and voltage being applied to the card, similar to the way in which a power supply normally turns on. Due to the controlled rise times and fall times of the AP2186/AP2196, these devices can be used to provide a softer start-up to devices being hot-plugged into a powered system. The UVLO feature of the AP2186/AP2196 also ensures that the switch is off after the card has been removed, and that the switch is off during the next insertion.

By placing the AP2186/AP2196 between the  $V_{CC}$  input and the rest of the circuitry, the input power reaches these devices first after insertion. The typical rise time of the switch is approximately 1ms, providing a slow voltage ramp at the output of the device. This implementation controls system surge current and provides a hot-plugging mechanism for any device.

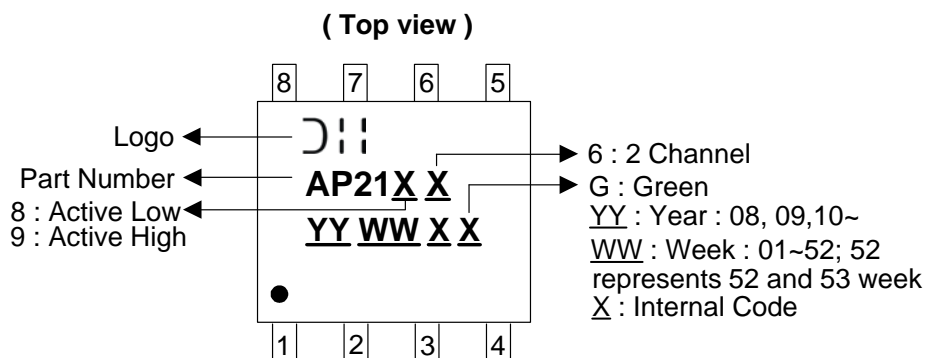
## Ordering Information



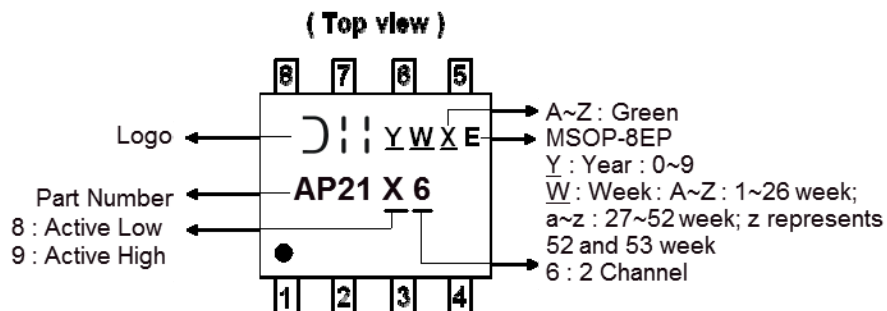
Part Number	Package Code	Packaging	13" Tape and Reel	
			Quantity	Part Number Suffix
AP21X6SG-13	S	SO-8	2500/Tape & Reel	-13
AP21X6MPG-13	MP	MSOP-8EP	2500/Tape & Reel	-13

## Marking Information

### (1) SO-8



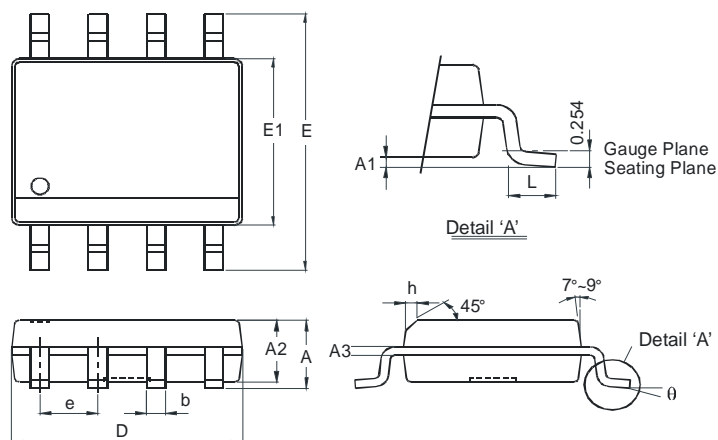
### (2) MSOP-8EP



## Package Outline Dimensions (All dimensions in mm.)

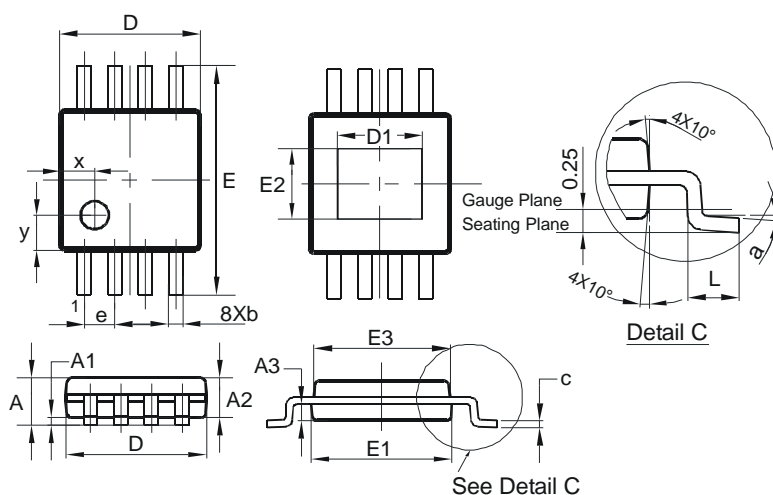
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.

### (1) Package Type: SO-8



SO-8		
Dim	Min	Max
A	-	1.75
A1	0.10	0.20
A2	1.30	1.50
A3	0.15	0.25
b	0.3	0.5
D	4.85	4.95
E	5.90	6.10
E1	3.85	3.95
e	1.27 Typ	
h	-	0.35
L	0.62	0.82
θ	0°	8°
All Dimensions in mm		

### (2) Package Type: MSOP-8EP



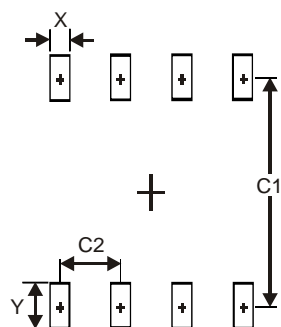
MSOP-8EP			
Dim	Min	Max	Typ
A	-	1.10	-
A1	0.05	0.15	0.10
A2	0.75	0.95	0.86
A3	0.29	0.49	0.39
b	0.22	0.38	0.30
c	0.08	0.23	0.15
D	2.90	3.10	3.00
D1	1.60	2.00	1.80
E	4.70	5.10	4.90
E1	2.90	3.10	3.00
E2	1.30	1.70	1.50
E3	2.85	3.05	2.95
e	-	-	0.65
L	0.40	0.80	0.60
a	0°	8°	4°
x	-	-	0.750
y	-	-	0.750
All Dimensions in mm			



## Suggested Pad Layout

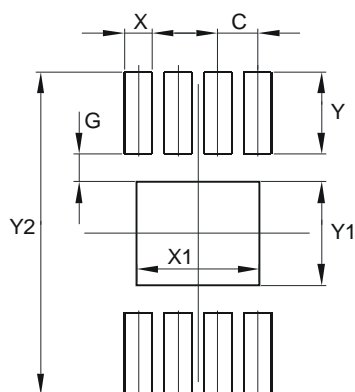
Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.

### (1) Package Type: SO-8



Dimensions	Value (in mm)
X	0.60
Y	1.55
C1	5.4
C2	1.27

### (2) Package Type: MSOP-8EP



Dimensions	Value (in mm)
C	0.650
G	0.450
X	0.450
X1	2.000
Y	1.350
Y1	1.700
Y2	5.300

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